# N-Channel 20-V (D-S) MOSFET

### **Key Features:**

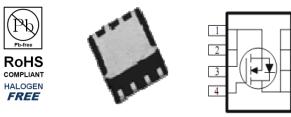
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY			
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
20	2.4 @ V <sub>GS</sub> = 4.5V	37	
20	3.5 @ V <sub>GS</sub> = 2.5V	31	

DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage	V <sub>DS</sub>	20	V			
Gate-Source Voltage	Voltage					
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I	37			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	30	А		
Pulsed Drain Current <sup>b</sup>	-	I <sub>DM</sub>	120			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	7.9	А		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	5	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	' D	3.2	٧V		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	25	°C/W		
	Steady State	ιν <sub>θ</sub> ja	65	C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

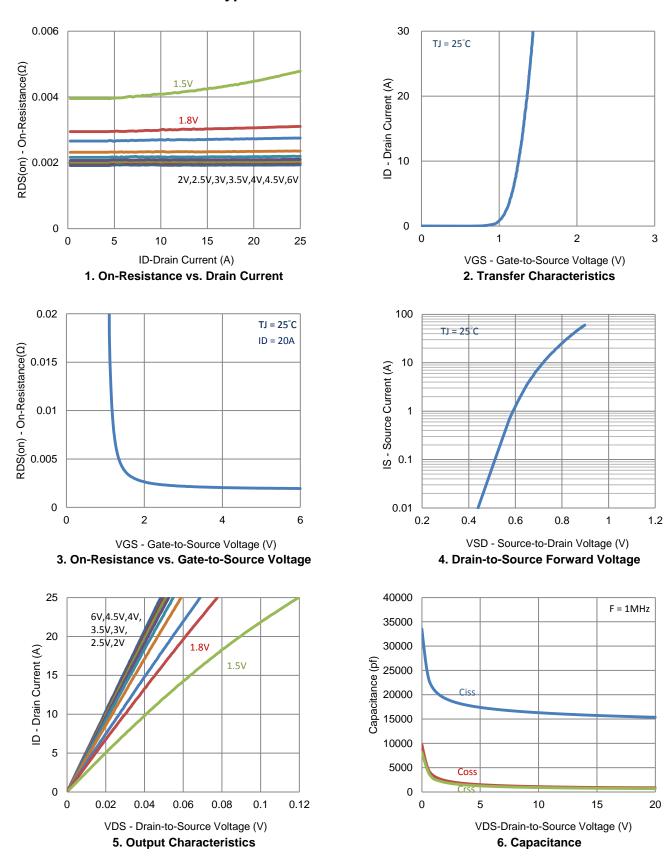
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$	1		1	uA	
	IDSS	$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	50			А	
Drain Course On Desistance a	r	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		2.4			
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 16 \text{ A}$			3.5	mΩ	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		14		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 4 \text{ A}, V_{GS} = 0 \text{ V}$		0.66		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Q <sub>g</sub>	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		134		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 V, V_{GS} = 4.3 V,$ $I_{D} = 20 A$		14			
Gate-Drain Charge	$Q_gd$	$I_D = 20$ A		32			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 10 \text{ V}, \text{ R}_{L} = 0.5 \Omega,$		29			
Rise Time	t <sub>r</sub>	$V_{DS} = 10 V, R_L - 0.5 \Omega,$ $I_D = 20 A,$		59		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		448		ns	
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 4.5 \text{ V},        $		140			
Input Capacitance	C <sub>iss</sub>			15736			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 Mhz		919		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			764			

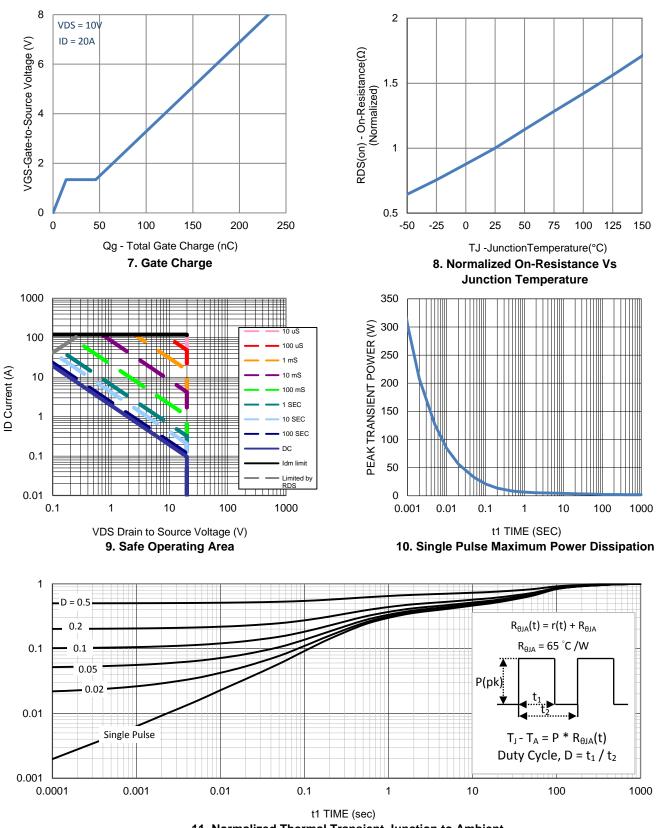
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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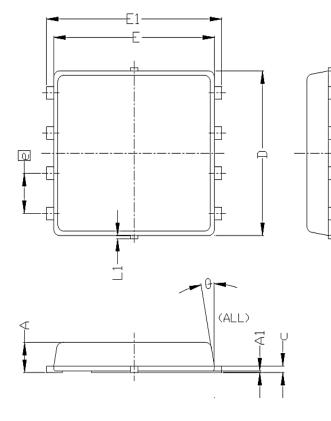
# **Typical Electrical Characteristics**

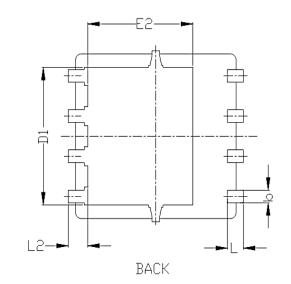


## **Typical Electrical Characteristics**

**11. Normalized Thermal Transient Junction to Ambient** 

# Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SIMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D		5.20 BSC			0. 205 BSC		
D1	4.35 BSC			0.171 BSC			
E	5.55 BSC			0.219 BSC			
E1	6.05 BSC			0.238 BSC			
E2		3. 62 BSC 0. 143 BSC					
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	